

New Jersey Semi-Conductor Products, Inc.

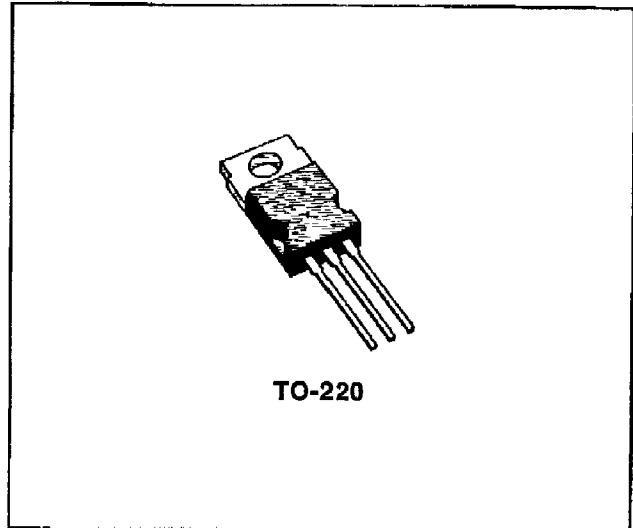
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BD705/706/707/708 BD709/710/711/712

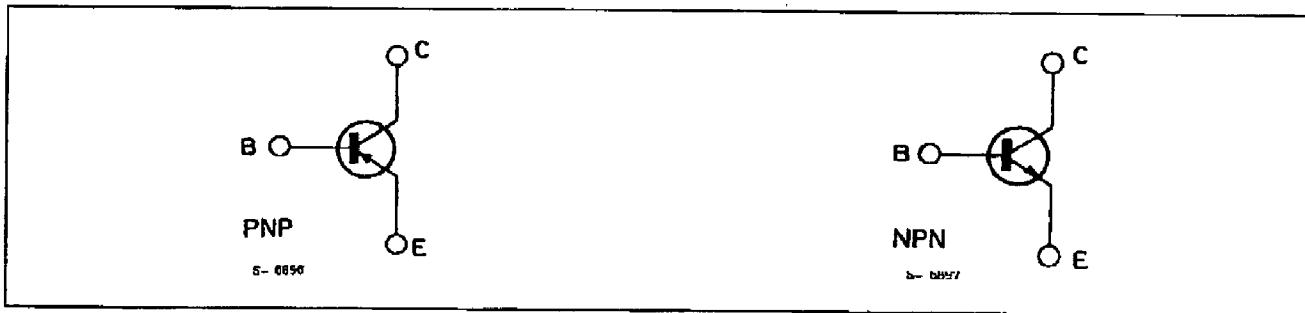
DESCRIPTION

The BD705, BD707, BD709 and BD711 are silicon epitaxial-base NPN power transistors in Jedec TO-220 plastic package intended for use in power linear and switching applications. The complementary PNP types are the BD706, BD708, BD710 and BD712 respectively.



TO-220

INTERNAL SCHEMATIC DIAGRAMS

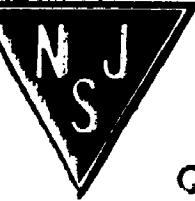


ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	NPN PNP*	Value				Unit
			BD705 BD706	BD707 BD708	BD709 BD710	BD711 BD712	
V_{CBO}	Collector-emitter Voltage ($I_E = 0$)		45	60	80	100	V
V_{CES}	Collector-emitter Voltage ($V_{BE} = 0$)		45	60	80	100	V
V_{CEO}	Collector-emitter Voltage ($I_B = 0$)		45	60	80	100	V
V_{EBO}	Emitter-base Voltage ($I_C = 0$)				5		V
I_C	Collector Current				12		A
I_B	Base Current				5		A
P_{tot}	Total Power Dissipation at $T_{case} \leq 25^\circ\text{C}$				75		W
T_{stg}	Storage Temperature				– 65 to 150		°C
T_j	Junction Temperature				150		°C

* For PNP types voltage and current values are negative.

NJ Semi-Conductors reserves the right to change test conditions, parameters limits and package dimensions without notice information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.



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ELECTRICAL CHARACTERISTICS ($T_{case} = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
I_{CEO}	Collector Cutoff Current ($I_E = 0$)	for BD705/706	$V_{CB} = 45\text{ V}$			100	μA
		for BD707/708	$V_{CB} = 60\text{ V}$			100	μA
		for BD709/710	$V_{CB} = 80\text{ V}$			100	μA
		for BD711/712	$V_{CB} = 100\text{ V}$			100	μA
		$T_{case} = 150^\circ\text{C}$					
		for BD705/706	$V_{CB} = 45\text{ V}$			1	mA
		for BD707/708	$V_{CB} = 60\text{ V}$			1	mA
		for BD709/710	$V_{CB} = 80\text{ V}$			1	mA
		for BD711/712	$V_{CB} = 100\text{ V}$			1	mA
I_{CEO}	Collector Cutoff Current ($I_B = 0$)	for BD705/706	$V_{CE} = 22\text{ V}$			1	mA
		for BD707/708	$V_{CE} = 30\text{ V}$			1	mA
		for BD709/710	$V_{CE} = 40\text{ V}$			1	mA
		for BD711/712	$V_{CE} = 50\text{ V}$			1	mA
I_{EBO}	Emitter Cutoff Current ($I_C = 0$)	$V_{EB} = 5\text{ V}$				1	mA
$V_{CEO(sus)}$ *	Collector-emitter Sustaining Voltage ($I_B = 0$)	$I_C = 100\text{ mA}$	for BD705/706	45			V
			for BD707/708	60			V
			for BD709/710	80			V
			for BD711/712	100			V
$V_{CE(sat)}$ *	Collector-emitter Saturation Voltage	$I_C = 4\text{ A}$	$I_B = 0.4\text{ A}$			1	V
V_{CEK} *	Knee Voltage	$I_C = 3\text{ A}$	$I_B = ^{**}$			0.4	V
V_{BE} *	Base-emitter-Voltage	$I_C = 4\text{ A}$	$V_{CE} = 4\text{ V}$			1.5	V
h_{FE} *	DC Current Gain	$I_C = 0.5\text{ A}$	$V_{CE} = 2\text{ V}$	40	120	400	
		$I_C = 2\text{ A}$	$V_{CE} = 2\text{ V}$				
			for BD705/706	30			
			for BD707/708	30			
			for BD709/710	30			
		$I_C = 4\text{ A}$	$V_{CE} = 4\text{ V}$				
			for BD705/706	20	30	150	
			for BD707/708	15		150	
			for BD709/710	15		150	
		$I_C = 10\text{ A}$	for BD711/712	15		150	
f_T	Transition Frequency	$I_C = 300\text{ mA}$	$V_{CE} = 3\text{ V}$	3			MHz

* Pulsed : pulse duration = 300 μs , duty cycle = 1.5 %.

** Value for which $I_0 = 3.3\text{A}$ at $V_{CE} = 2\text{V}$.

For PNP types voltage and current values are negative.